

Trench gate field-stop IGBT, HB series 650 V, 40 A high speed

Datasheet - production data

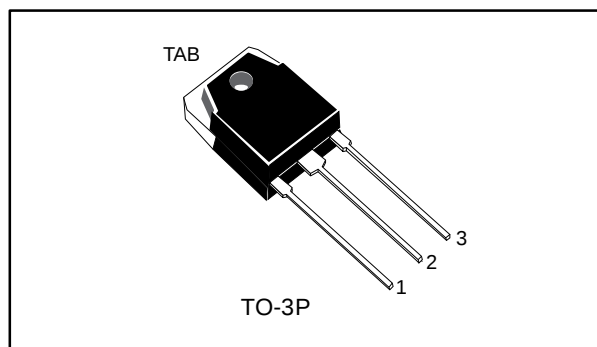
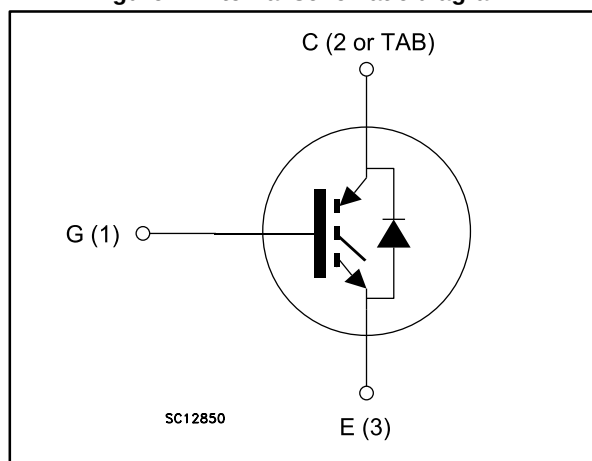


Figure 1: Internal schematic diagram



Features

- Maximum junction temperature: $T_J = 175\text{ }^{\circ}\text{C}$
- Minimized tail current
- $V_{CE(sat)} = 1.6\text{ V (typ.) @ } I_C = 40\text{ A}$
- Tight parameter distribution
- Co-packed diode for protection
- Safe paralleling
- Low thermal resistance

Applications

- Power factor corrector (PFC)

Description

This device is an IGBT developed using an advanced proprietary trench gate field-stop structure. The device is part of the new HB series of IGBTs, which represents an optimum compromise between conduction and switching loss to maximize the efficiency of any frequency converter. Furthermore, the slightly positive $V_{CE(sat)}$ temperature coefficient and very tight parameter distribution result in safer paralleling operation.

Table 1: Device summary

Order code	Marking	Package	Packing
STGWT40HP65FB	GWT40HP65FB	TO-3P	Tube

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage ($V_{GE} = 0$ V)	650	V
I_C	Continuous collector current at $T_C = 25$ °C	80	A
	Continuous collector current at $T_C = 100$ °C	40	
$I_{CP}^{(1)}$	Pulsed collector current	160	A
V_{GE}	Gate-emitter voltage	± 30	V
$I_F^{(2)}$	Continuous forward current at $T_C = 25$ °C	5	A
	Continuous forward current at $T_C = 100$ °C	5	
$I_{FP}^{(3)}$	Pulsed forward current	10	A
P_{TOT}	Total dissipation at $T_C = 25$ °C	283	W
T_{STG}	Storage temperature range	- 55 to 150	°C
T_J	Operating junction temperature range	- 55 to 175	

Notes:

⁽¹⁾Pulse width limited by maximum junction temperature.

⁽²⁾Limited by wires.

⁽³⁾Pulsed forward current.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case IGBT	0.53	°C/W
R_{thJC}	Thermal resistance junction-case diode	5	
R_{thJA}	Thermal resistance junction-ambient	50	

2 Electrical characteristics

$T_J = 25\text{ °C}$ unless otherwise specified

Table 4: Static characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}$, $I_C = 2\text{ mA}$	650			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 40\text{ A}$		1.6	2.0	V
		$V_{GE} = 15\text{ V}$, $I_C = 40\text{ A}$, $T_J = 125\text{ °C}$		1.7		
		$V_{GE} = 15\text{ V}$, $I_C = 40\text{ A}$, $T_J = 175\text{ °C}$		1.8		
V_F	Forward on-voltage	$I_F = 5\text{ A}$		2		V
		$I_F = 5\text{ A}$, $T_J = 125\text{ °C}$		1.85		
		$I_F = 5\text{ A}$, $T_J = 175\text{ °C}$		1.75		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 1\text{ mA}$	5	6	7	V
I_{CES}	Collector cut-off current	$V_{GE} = 0\text{ V}$, $V_{CE} = 650\text{ V}$			25	μA
I_{GES}	Gate-emitter leakage current	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			± 250	nA

Table 5: Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0\text{ V}$	-	5412	-	pF
C_{oes}	Output capacitance		-	198	-	
C_{res}	Reverse transfer capacitance		-	107	-	
Q_g	Total gate charge	$V_{CC} = 520\text{ V}$, $I_C = 40\text{ A}$, $V_{GE} = 15\text{ V}$ (see Figure 29: "Gate charge test circuit")	-	210	-	nC
Q_{ge}	Gate-emitter charge		-	39	-	
Q_{gc}	Gate-collector charge		-	82	-	

Table 6: IGBT switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-delay time	$V_{CE} = 400\text{ V}$, $I_C = 40\text{ A}$, $V_{GE} = 15\text{ V}$, $R_G = 5\text{ }\Omega$ (see Figure 28: "Test circuit for inductive load switching")	-	142	-	ns
t_f	Current fall time		-	27	-	ns
$E_{off}^{(1)}$	Turn-off switching energy		-	363	-	μJ
$t_{d(off)}$	Turn-off-delay time	$V_{CE} = 400\text{ V}$, $I_C = 40\text{ A}$, $V_{GE} = 15\text{ V}$, $R_G = 5\text{ }\Omega$, $T_J = 175\text{ °C}$ (see Figure 28: "Test circuit for inductive load switching")	-	141	-	ns
t_f	Current fall time		-	61	-	ns
E_{off}	Turn-off switching energy		-	764	-	μJ

Notes:

⁽¹⁾Including the tail of the collector current.

Table 7: Diode switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$I_F = 5\text{ A}$, $V_R = 400\text{ V}$, $V_{GE} = 15\text{ V}$ (see Figure 28: "Test circuit for inductive load switching") $di/dt = 1000\text{ A}/\mu\text{s}$	-	140		ns
Q_{rr}	Reverse recovery charge		-	21		nC
I_{rrm}	Reverse recovery current		-	6.6		A
di_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	430		A/ μs
E_{rr}	Reverse recovery energy		-	1.6		μJ
t_{rr}	Reverse recovery time	$I_F = 5\text{ A}$, $V_R = 400\text{ V}$, $V_{GE} = 15\text{ V}$ $T_J = 175\text{ }^\circ\text{C}$ (see Figure 28: "Test circuit for inductive load switching") $di/dt = 1000\text{ A}/\mu\text{s}$	-	200		ns
Q_{rr}	Reverse recovery charge		-	47.3		nC
I_{rrm}	Reverse recovery current		-	9.6		A
di_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	428		A/ μs
E_{rr}	Reverse recovery energy		-	3.2		μJ

2.1 Electrical characteristics (curves)

Figure 2: Power dissipation vs. case temperature

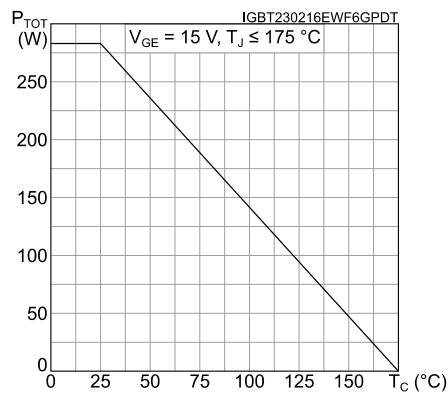


Figure 3: Collector current vs. case temperature

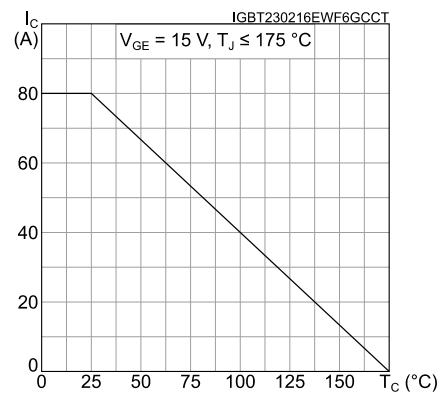


Figure 4: Output characteristics (T_J = 25°C)

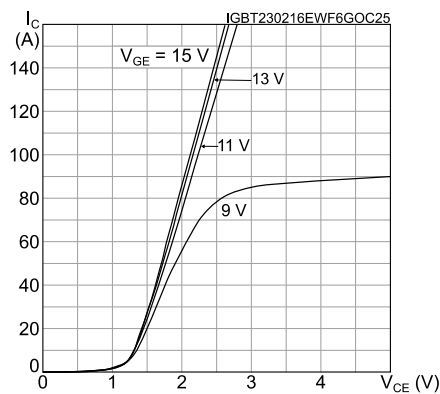


Figure 5: Output characteristics (T_J = 175°C)

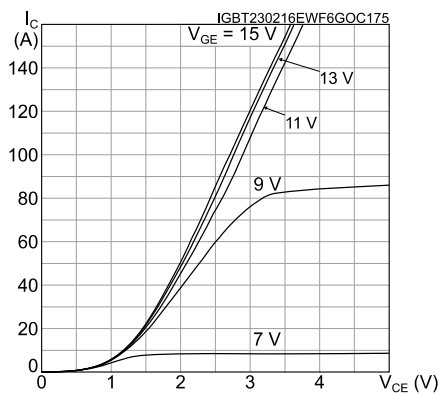


Figure 6: V_{CE(sat)} vs. junction temperature

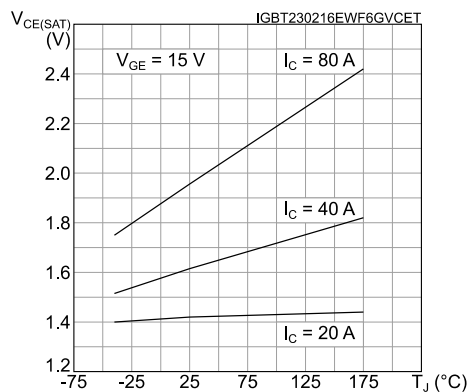


Figure 7: V_{CE(sat)} vs. collector current

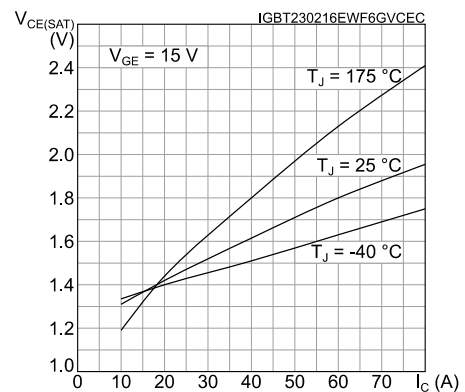


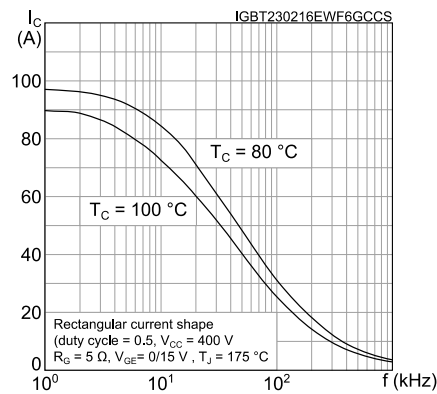
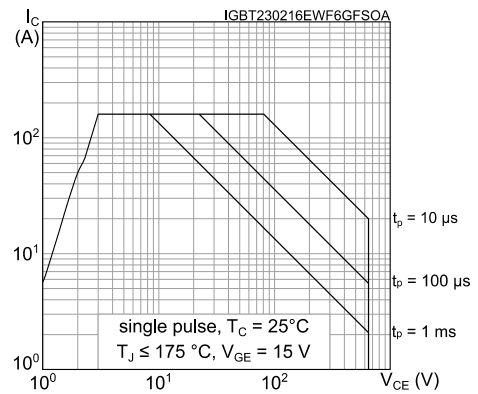
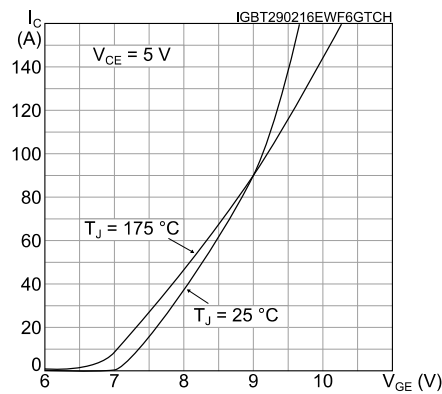
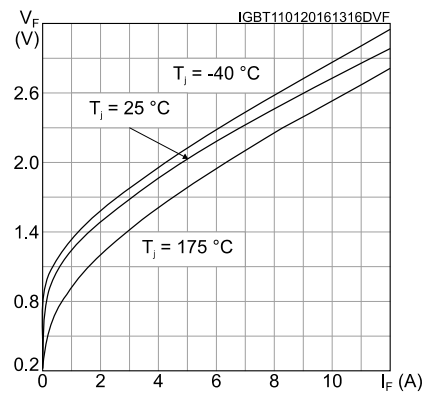
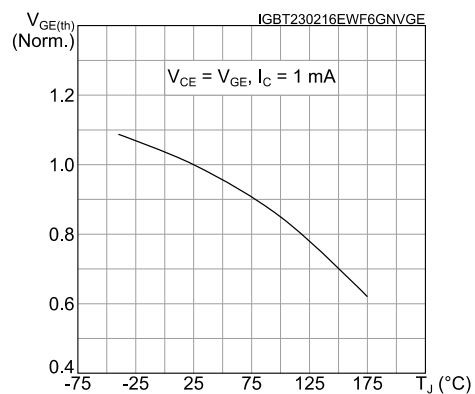
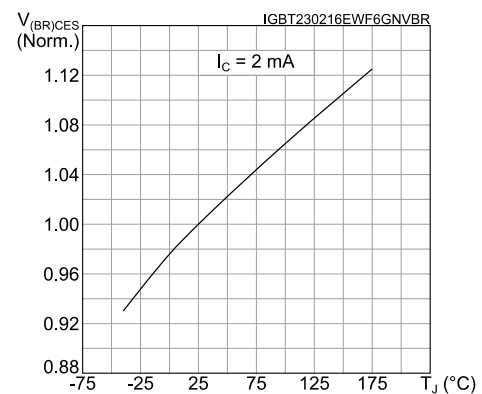
Figure 8: Collector current vs. switching frequency**Figure 9: Forward bias safe operating area****Figure 10: Transfer characteristics****Figure 11: Diode VF vs. forward current****Figure 12: Normalized V_GE(th) vs junction temperature****Figure 13: Normalized V(BR)CES vs. junction temperature**

Figure 14: Capacitance variations

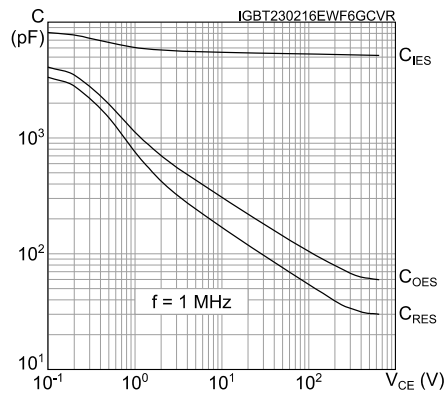


Figure 15: Gate charge vs. gate-emitter voltage

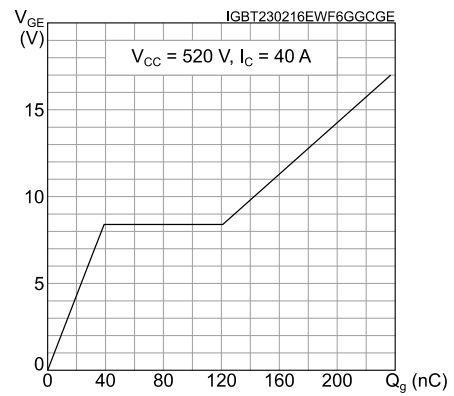


Figure 16: Switching energy vs collector current

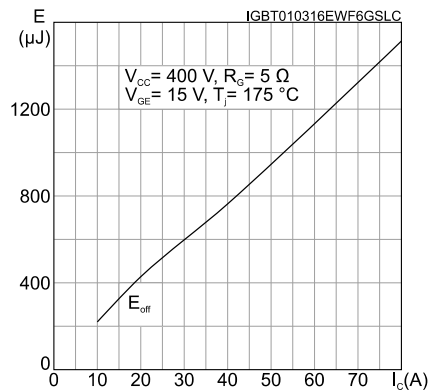


Figure 17: Switching energy vs gate resistance

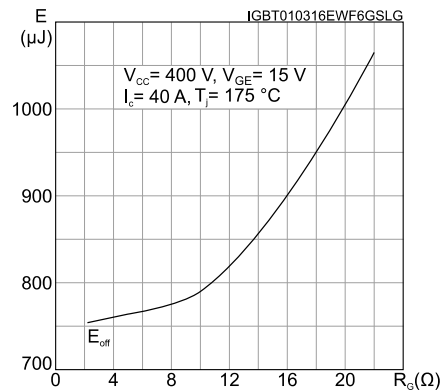


Figure 18: Switching energy vs temperature

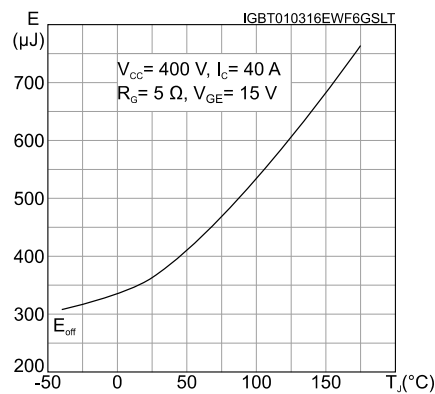


Figure 19: Switching energy vs. collector emitter voltage

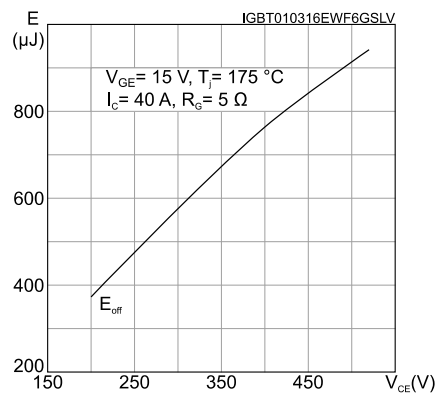


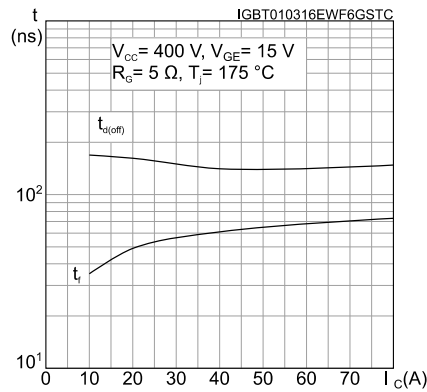
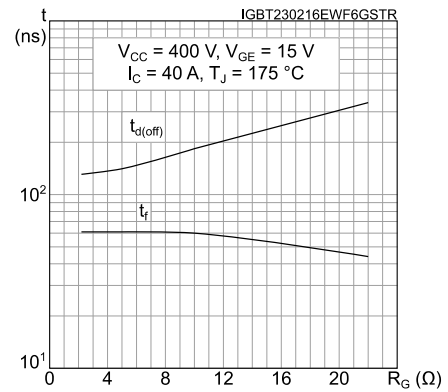
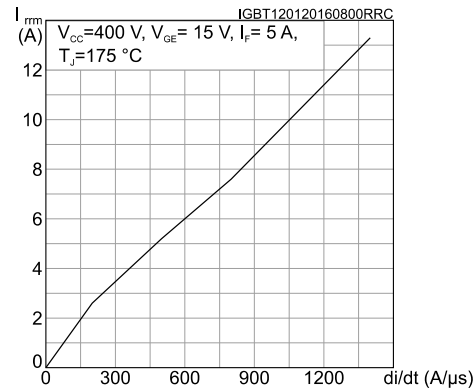
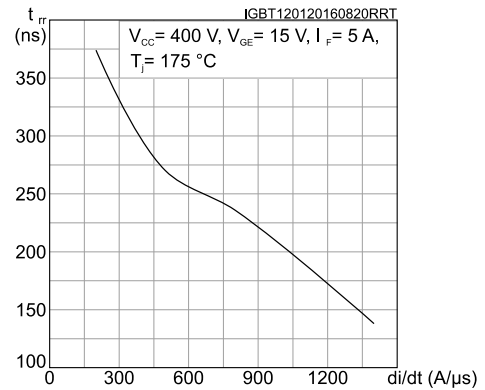
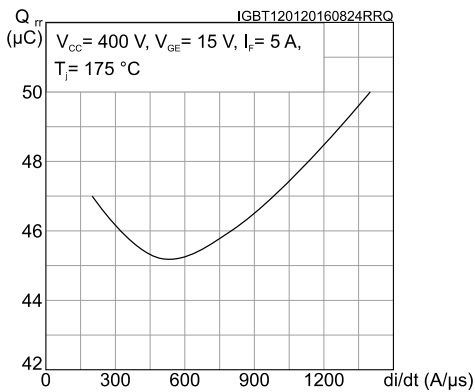
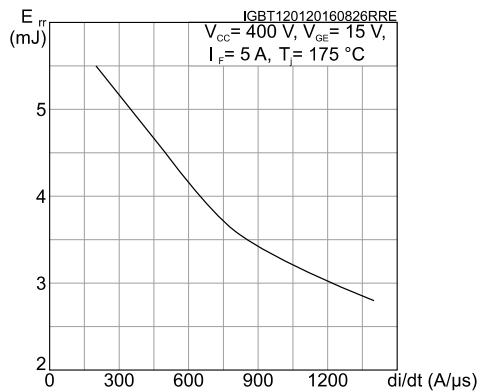
Figure 20: Switching times vs. collector current**Figure 21: Switching times vs. gate resistance****Figure 22: Reverse recovery current vs. diode current slope****Figure 23: Reverse recovery time vs. diode current slope****Figure 24: Reverse recovery charge vs. diode current slope****Figure 25: Reverse recovery energy vs. diode current slope**

Figure 26: Thermal impedance

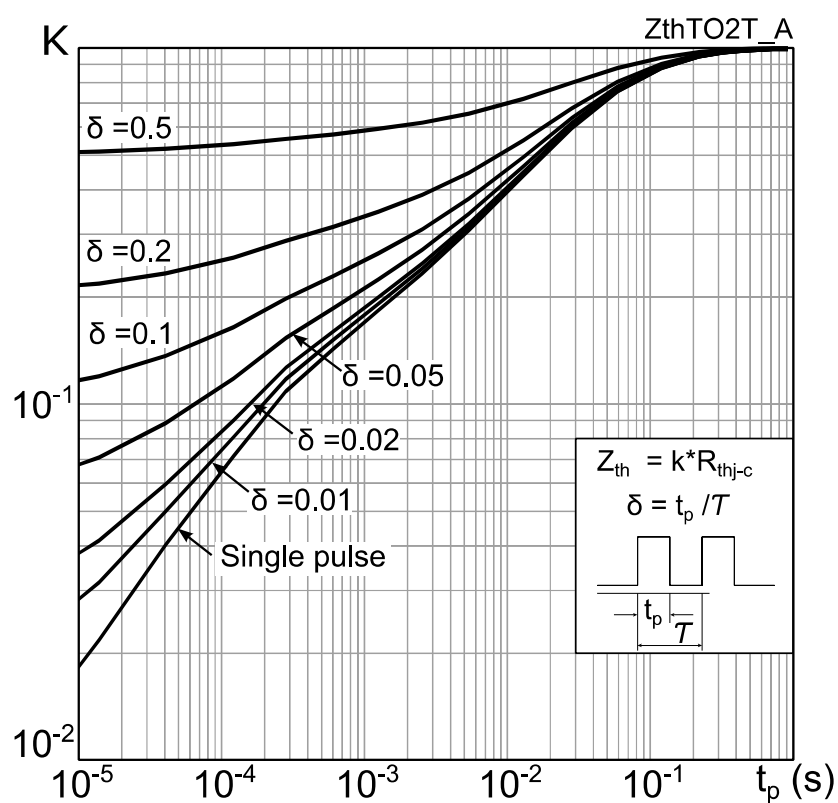
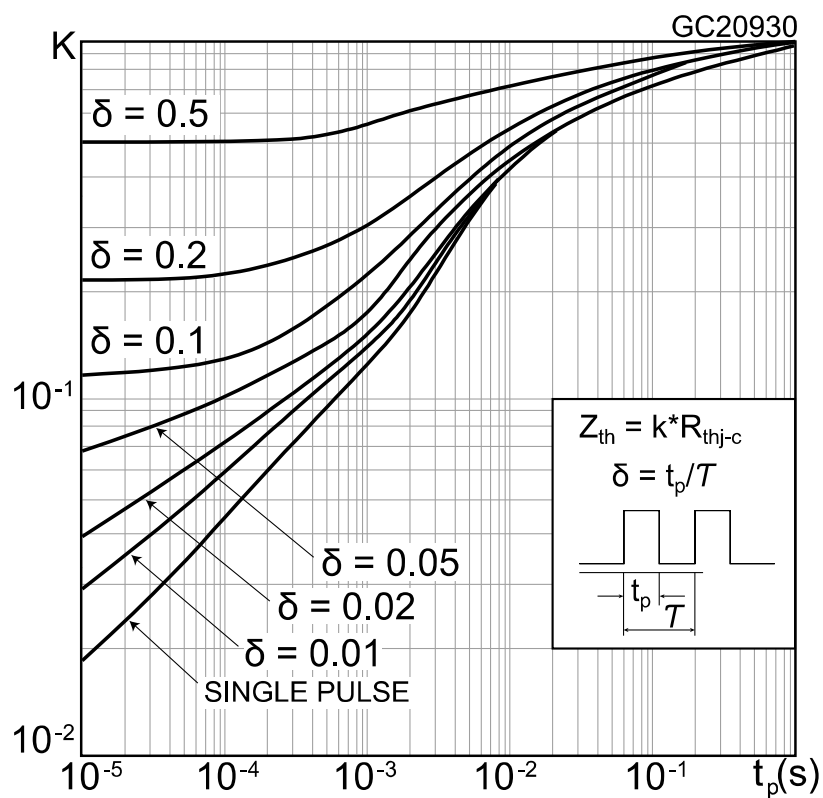


Figure 27: Thermal impedance for diode



3 Test circuits

Figure 28: Test circuit for inductive load switching

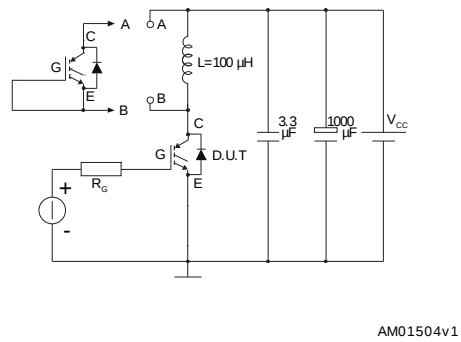


Figure 29: Gate charge test circuit

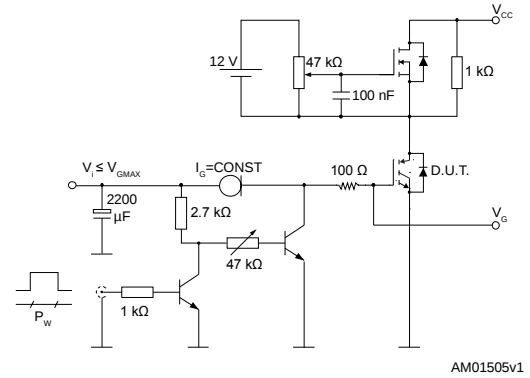
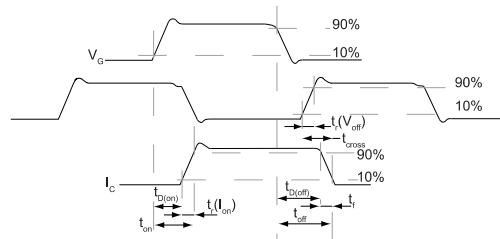


Figure 30: Switching waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

4.1 TO-3P package information

Figure 31: TO-3P package outline

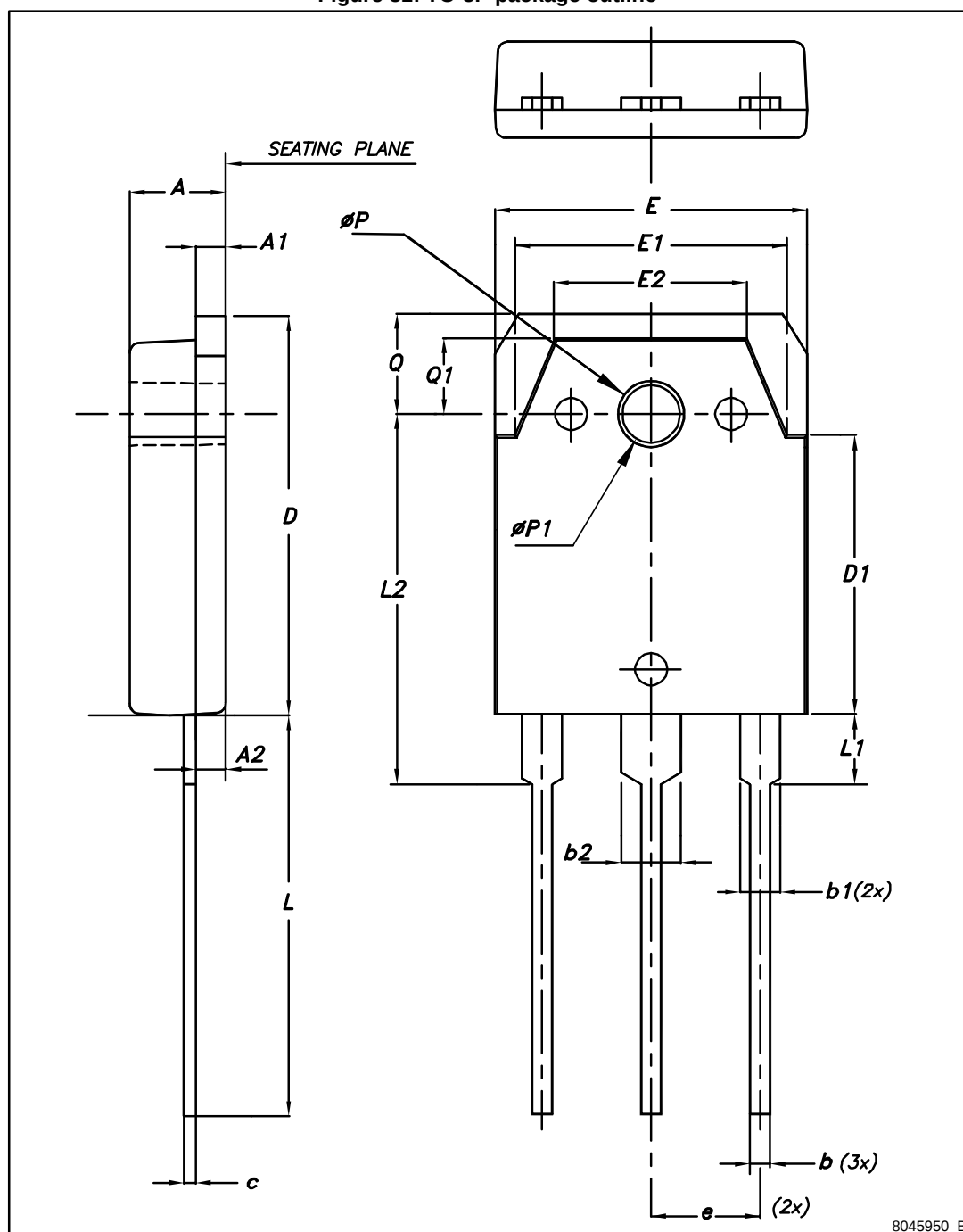


Table 8: TO-3P package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.60	4.80	5.00
A1	1.45	1.50	1.65
A2	1.20	1.40	1.60
b	0.80	1.00	1.20
b1	1.80	2.00	2.20
b2	2.80	3.00	3.20
c	0.55	0.60	0.75
D	19.70	19.90	20.10
D1	13.70	13.90	14.10
E	15.40	15.60	15.80
E1	13.40	13.60	13.80
E2	9.40	9.60	9.90
e	5.15	5.45	5.75
L	19.80	20.00	20.20
L1	3.30	3.50	3.70
L2	18.20	18.40	18.60
ØP	3.30	3.40	3.50
ØP1	3.10	3.20	3.30
Q	4.80	5.00	5.20
Q1	3.60	3.80	4

5 Revision history

Table 9: Document revision history

Date	Revision	Changes
20-Oct-2015	1	First release.
01-Mar-2016	2	Updated features in cover page. Inserted <i>Section 2.1: "Electrical characteristics (curves)"</i> . Minor text changes
13-Jul-2016	3	Document status promoted from preliminary to production data.

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